

Status of 3D Detectors TCAD Simulations

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We will present our results with TCAD Simulations of three different 3D Devices (ROC4Sense, Fermilab, PSI46). We have I-V, C-V and MIP simulations before and after irradiation up to $2 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$. Also include will be a glimpse of our present effort for LGAD device simulations on MIP hit.

Summary

TCAD Simulations (IV, CV, MIP, Irradiated (IV, CV, MIP)) of 3D Detectors

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